



## DESCRIPTION

The TVS16H5.0 is available in DFN1610-2 Package

## FEATURES

- 5V uni-directional ESD diode
- Low clamping voltage
- Complies with IEC 61000-4-2 standards:
  - Air discharge:  $\pm 30\text{kV}$
  - Contact discharge:  $\pm 30\text{kV}$
- Available in DFN1610-2 Package

## ORDERING INFORMATION

Package Type	Part Number
DFN1610-2	TVS16H5.0
Note	SPQ: 8,000pcs/Reel
AiT provides all RoHS Compliant Products	

## PIN DESCRIPTION





## ABSOLUTE MAXIMUM RATINGS

T<sub>A</sub>=25°C, unless otherwise specified

P <sub>PK</sub> , Peak Pulse Power (8/20μs)	1250W
I <sub>PP</sub> , Peak Pulse Current (8/20μs)	100A
T <sub>J</sub> , Operating Temperature Range	-55°C ~125°C
T <sub>STG</sub> , Storage Temperature Range	-55°C ~150°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## ELECTRICAL CHARACTERISTICS

T<sub>A</sub> = 25°C, unless otherwise noted

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Reverse Working Voltage	V <sub>RWM</sub>		-	-	5	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> = 1mA	6	-	7.8	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>R</sub> = 5V	-	-	2	μA
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> =10A (8 x 20μs pulse)	-	-	8.5	V
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> = 80A (8 x 20μs pulse)	-	-	15	V
Junction Capacitance	C <sub>J</sub>	V <sub>R</sub> = 0V, f = 1MHz	-	-	800	pF

NOTE: Electrical parameters are only for die, performance may alter after assembly



## TYPICAL CHARACTERISTICS

$T_A = 25^\circ\text{C}$ , unless otherwise noted

Figure 1. Junction Capacitance vs. Reverse Voltage

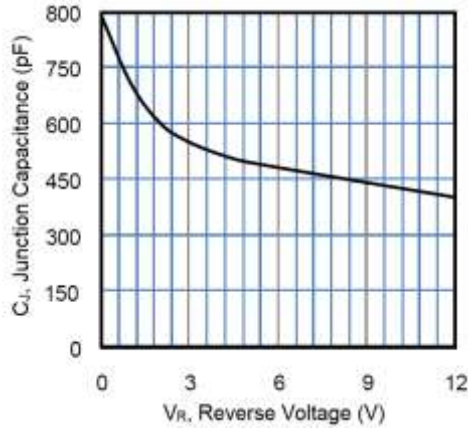


Figure 2. Clamping Voltage vs. Peak Pulse Current

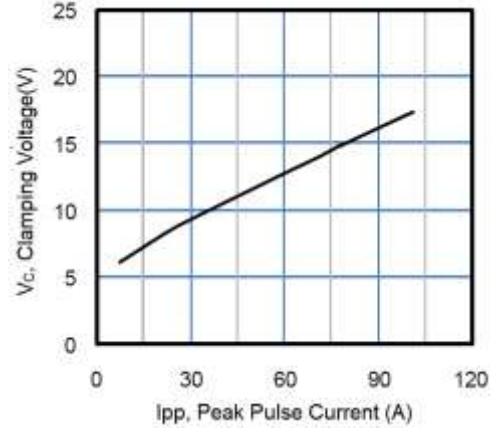


Figure 3. 8 X 20us Pulse Waveform

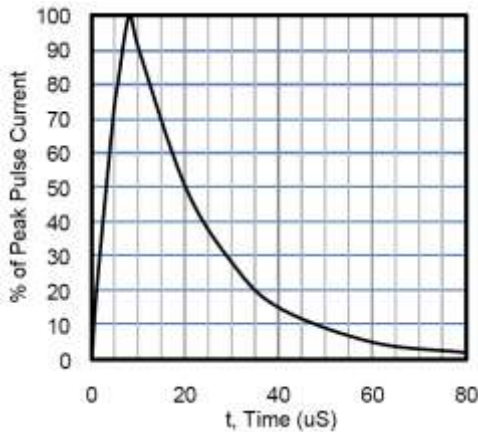


Figure 4. Power Derating Curve

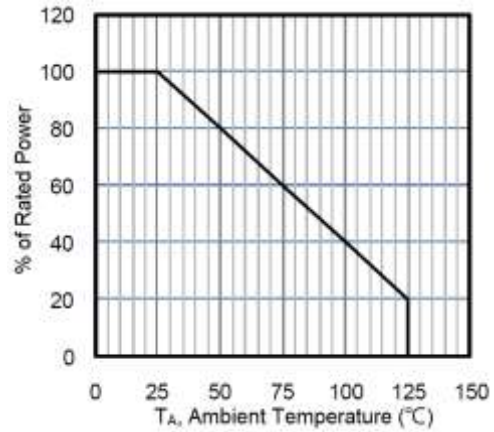


Figure 5. ESD Clamping Voltage

Positive 8 kV Contact per IEC61000-4-2

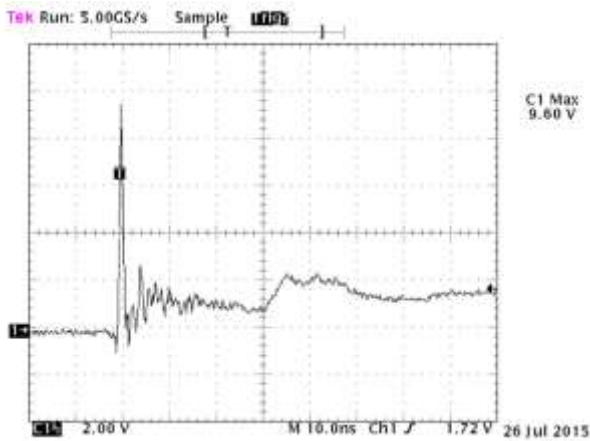
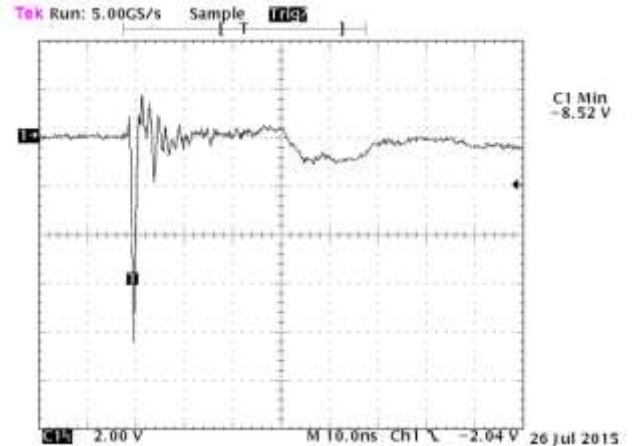


Figure 6. ESD Clamping Voltage

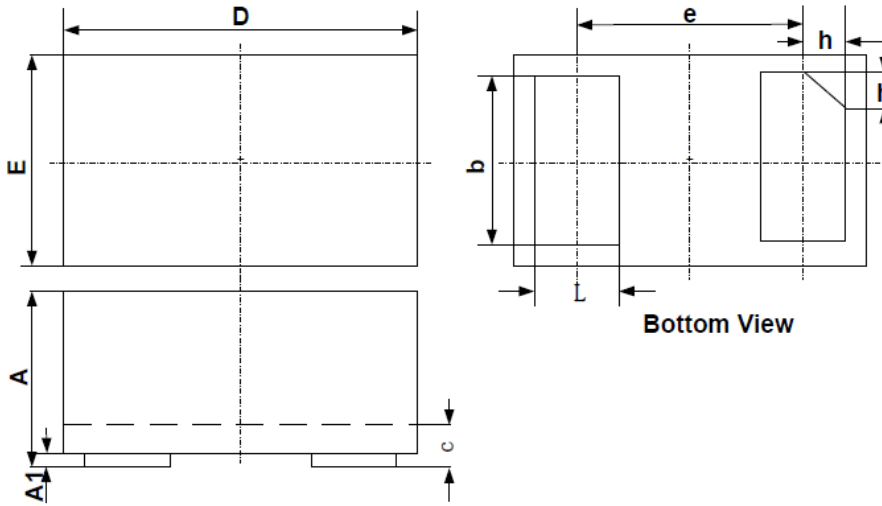
Negative 8 kV Contact per IEC61000-4-2



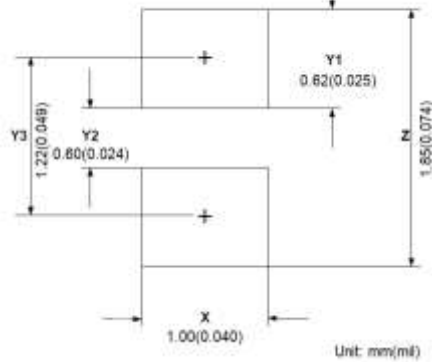


## PACKAGE INFORMATION

Dimension in DFN1610-2 Package (Unit: mm)



### Suggested Land Pattern



Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.45	0.55	0.018	0.022
A1	0.00	0.05	0.000	0.002
b	0.75	0.85	0.030	0.034
c	0.10	0.20	0.004	0.008
D	1.55	1.65	0.062	0.066
e	1.10BSC		0.044BSC	
E	0.95	1.05	0.038	0.042
L	0.35	0.45	0.014	0.018
h	0.15	0.25	0.006	0.010



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